

PRELIMINARY
 Notice: This is not a final specification.
 Some parametric limits are subject to change.

MITSUBISHI Pch POWER MOSFET

FX20ASJ-2

HIGH-SPEED SWITCHING USE

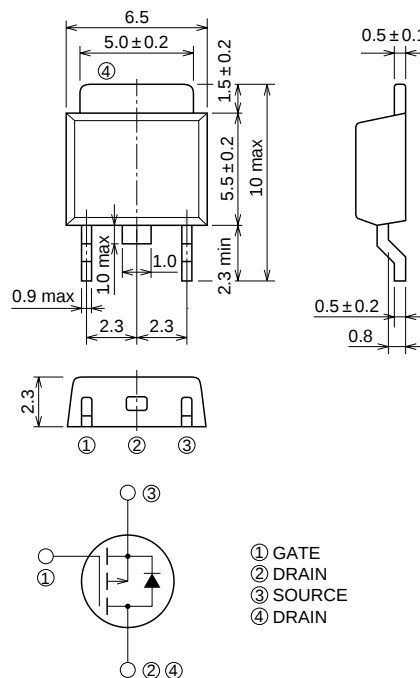
FX20ASJ-2



- 4V DRIVE
- V_{DS} -100V
- $r_{DS(ON)}$ (MAX) 0.26Ω
- I_D -20A
- Integrated Fast Recovery Diode (TYP.) 100ns

OUTLINE DRAWING

Dimensions in mm



MP-3

APPLICATION

Motor control, Lamp control, Solenoid control
 DC-DC converter, etc.

MAXIMUM RATINGS (Tc = 25°C)

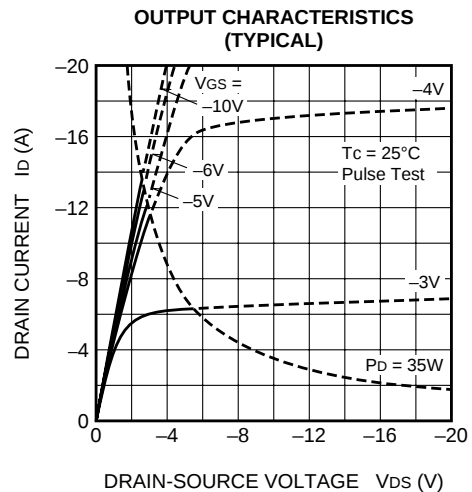
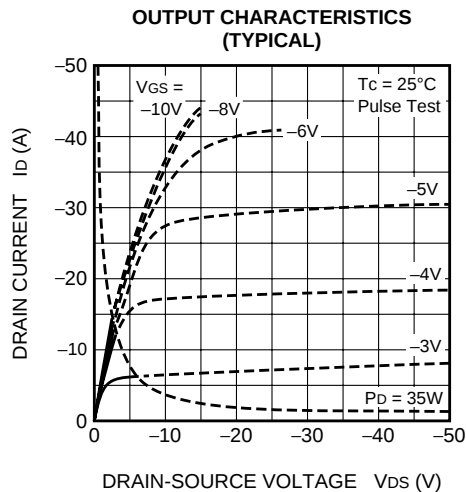
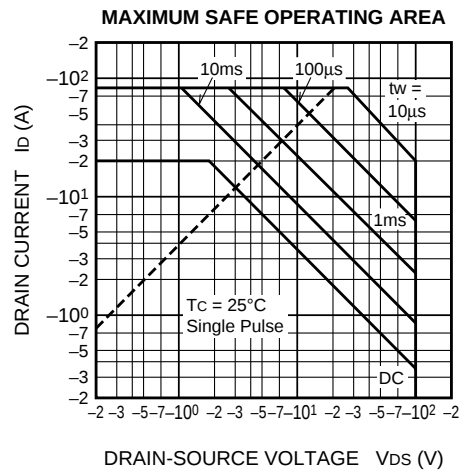
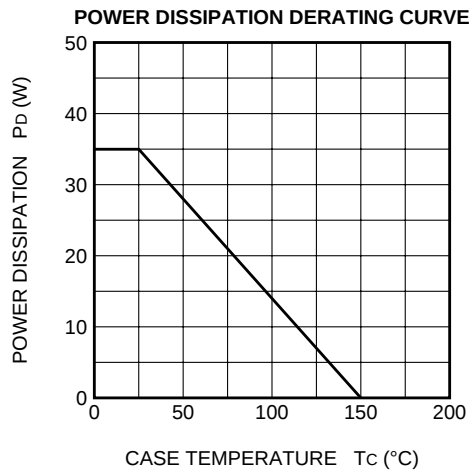
Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	-100	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		-20	A
I_{DM}	Drain current (Pulsed)		-80	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 50\mu H$	-20	A
I_S	Source current		-20	A
I_{SM}	Source current (Pulsed)		-80	A
P_D	Maximum power dissipation		35	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.26	g

Jan.1999

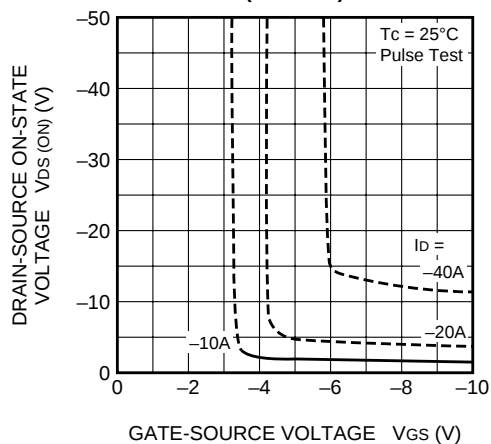
ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = -1mA, VGS = 0V	-100	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = -100V, VGS = 0V	—	—	-0.1	mA
VGS (th)	Gate-source threshold voltage	Id = -1mA, VDS = -10V	-1.0	-1.5	-2.0	V
rDS (ON)	Drain-source on-state resistance	Id = -10A, VGS = -10V	—	0.20	0.26	Ω
rDS (ON)	Drain-source on-state resistance	Id = -10A, VGS = -4V	—	0.25	0.32	Ω
VDS (ON)	Drain-source on-state voltage	Id = -10A, VGS = -10V	—	-2.0	-2.6	V
yfs	Forward transfer admittance	Id = -10A, VDS = -10V	—	10.3	—	S
Ciss	Input capacitance	VDS = -10V, VGS = 0V, f = 1MHz	—	2360	—	pF
Coss	Output capacitance		—	198	—	pF
Crss	Reverse transfer capacitance		—	99	—	pF
td (on)	Turn-on delay time	VDD = -50V, Id = -10A, VGS = -10V, RGEN = RGS = 50Ω	—	13	—	ns
tr	Rise time		—	30	—	ns
td (off)	Turn-off delay time		—	139	—	ns
tf	Fall time		—	74	—	ns
VSD	Source-drain voltage	IS = -10A, VGS = 0V	—	-1.0	-1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	3.57	°C/W
trr	Reverse recovery time	IS = -20A, dis/dt = 100A/μs	—	100	—	ns

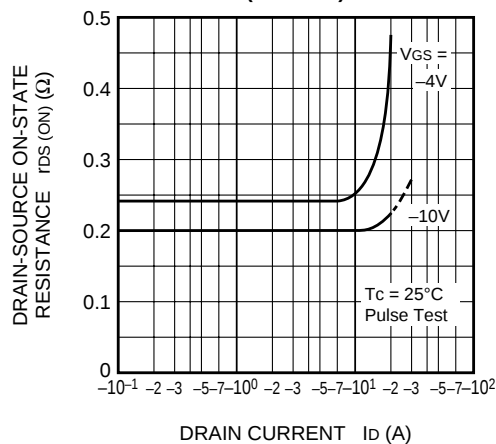
PERFORMANCE CURVES



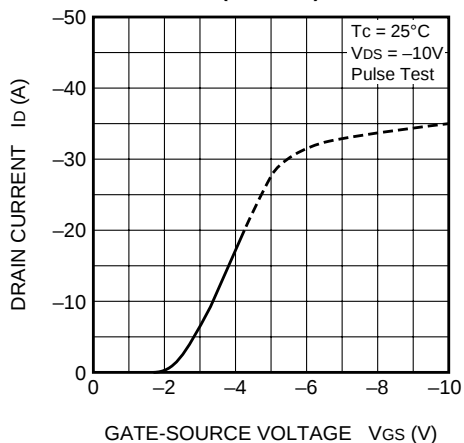
**ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)**



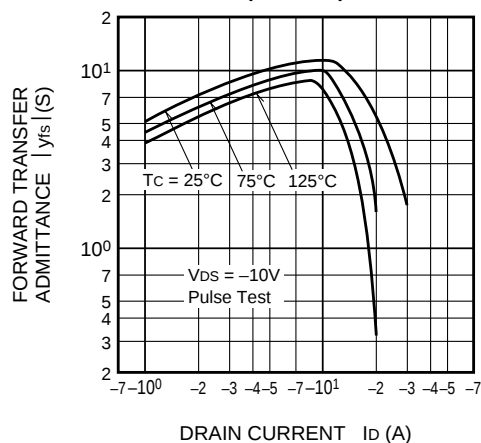
**ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)**



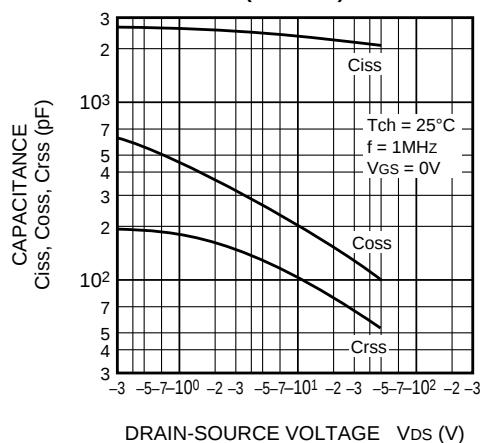
**TRANSFER CHARACTERISTICS
(TYPICAL)**



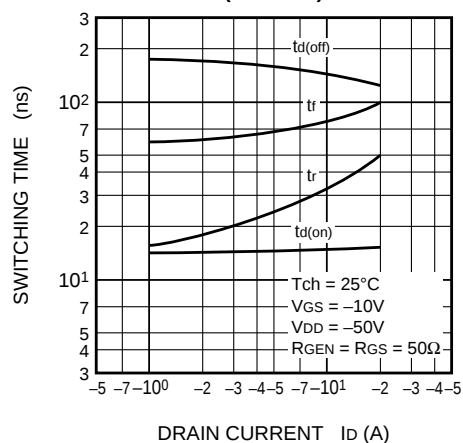
**FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)**



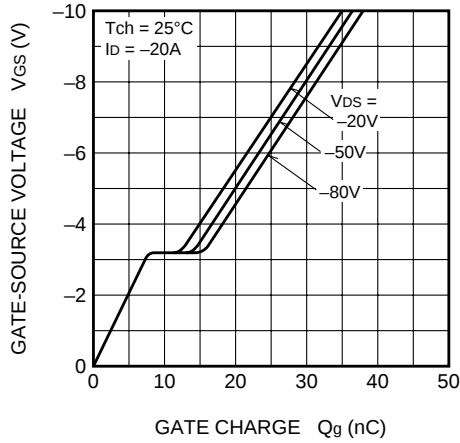
**CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)**



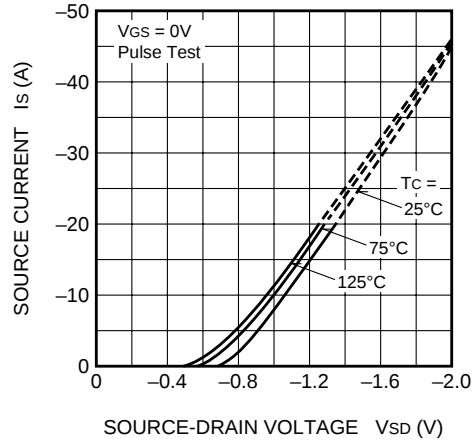
**SWITCHING CHARACTERISTICS
(TYPICAL)**



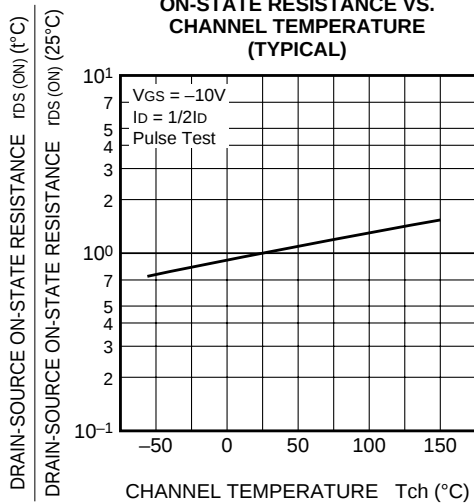
**GATE-SOURCE VOLTAGE
 VS. GATE CHARGE
 (TYPICAL)**



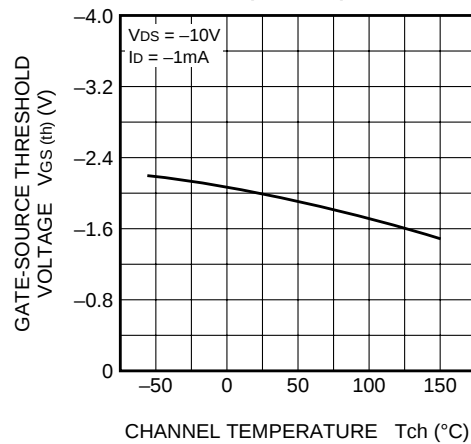
**SOURCE-DRAIN DIODE
 FORWARD CHARACTERISTICS
 (TYPICAL)**



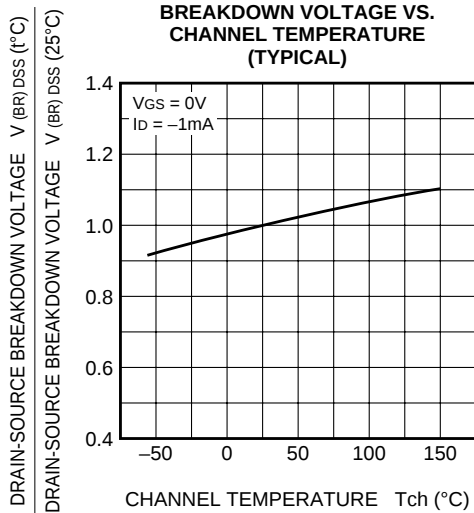
**ON-STATE RESISTANCE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**THRESHOLD VOLTAGE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**BREAKDOWN VOLTAGE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
 CHARACTERISTICS**

